BLS9G2934L-400; BLS9G2934LS-400 LDMOS S-band radar power transistor

AMMPLEON

Rev. 1 — 6 April 2017

Product data sheet

Product profile

1.1 General description

Single ended 400 W LDMOS power transistor for S-band radar applications in the frequency range from 2.9 GHz to 3.4 GHz.

Typical performance Table 1.

Typical RF performance at T_{case} = 25 °C; t_{p} = 300 μs ; δ = 10 %; I_{Dq} = 400 mA; in a class-AB demo test circuit.

Test signal	f	V _{DS}	P _{L(1dB)}	Gp	η_{D}
	(GHz)	(V)	(W)	(dB)	(%)
pulsed RF	2.9 to 3.4	32	400	12	43

1.2 Features and benefits

- Single ended
- Small size
- High efficiency
- Excellent ruggedness
- Designed for S-band operation
- Excellent thermal stability
- Easy power control
- Integrated dual sided ESD protection enables excellent off-state isolation
- High flexibility with respect to pulse formats
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

■ S-band radar applications in the frequency range 2.9 GHz to 3.4 GHz

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLS9G2934	IL-400 (SOT502A)		
1	drain		
2	gate	5 3	1
3	source [1]		2 3 sym112
BLS9G2934	ILS-400 (SOT502B)		
1	drain		
2	gate	1 3	1
3	source [1]	2	2 3 sym112

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BLS9G2934L-400	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT502A		
BLS9G2934LS-400	-	earless flanged ceramic package; 2 leads	SOT502B		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter		Max	Unit
V _{DS} drain-source voltage		-	65	V
V_{GS}	gate-source voltage	-6	+11	V
T _{stg}	storage temperature	- 65	+150	°C
Tj	junction temperature [1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$Z_{\text{th(j-case)}}$	transient thermal impedance from junction	$T_{case} = 85 ^{\circ}C; P_{L} = 400 W$		
	to case	t_p = 100 μ s; δ = 10 %	0.11	K/W
		t_p = 200 μ s; δ = 10 %	0.13	K/W
		t_p = 300 μ s; δ = 10 %	0.15	K/W
		$t_p = 500 \ \mu s; \ \delta = 10 \ \%$	0.17	K/W
		t_p = 1 ms; δ = 10 %	0.18	K/W
		t_p = 100 μs ; δ = 20 %	0.15	K/W

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 4.5 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 450 mA	1.5	2.0	3.1	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	85	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	400	nA
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 450 mA	-	4.1	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 15.75 A$	-	0.030	0.060	Ω

Table 7. RF characteristics

Test signal: pulsed RF; 2.9 GHz \leq f \leq 3.4 GHz; t_p = 300 μ s; δ = 10 %; RF performance at V_{DS} = 32 V; I_{Dq} = 400 mA; T_{case} = 25 °C; unless otherwise specified, in a class-AB narrow band production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _L = 400 W	10	11	-	dB
η_{D}	drain efficiency	P _L = 400 W	40	43	-	%
RLin	input return loss	P _L = 400 W	-	-8	-	dB
P _{droop(pulse)}	pulse droop power	P _L = 400 W	-	0.15	0.5	dB
t _r	rise time	P _L = 400 W	-	6	50	ns
t _f	fall time	P _L = 400 W	-	6	50	ns
P _{L(2dB)}	output power at 2 dB gain compression		400	-	-	W

7. Test information

7.1 Ruggedness in class-AB operation

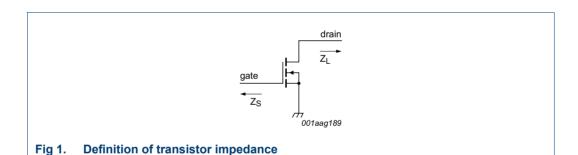
The BLS9G2934L-400 and BLS9G2934LS-400 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq} = 400 mA; P_{L} = 400 W; I_{Dq} = 300 I_{LS} ; I_{Dq} = 400 mA; I_{Dq} = 400 m

7.2 Impedance information

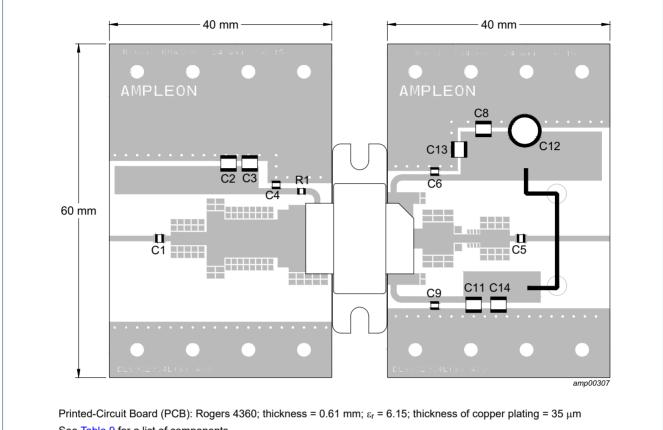
Table 8. Typical impedance

f	Z _S [1]	Z _L [1]
(GHz)	(Ω)	(Ω)
2.9	1.24 – j5.79	1.10 – j3.97
3.0	3.36 – j6.81	1.74 – j3.98
3.1	7.10 – j3.33	2.49 – j3.43
3.2	3.51 – j0.05	2.50 – j3.43
3.3	1.74 – j0.92	2.76 – j3.70
3.4	1.31 – j1.89	1.89 – j3.16

[1] Impedances are taken at a single halve of the push-pull transistor



7.3 Test circuit



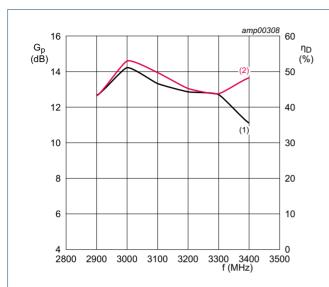
See Table 9 for a list of components.

Fig 2. Component layout for class-AB production test circuit

List of components Table 9. For test circuit see Figure 2.

Component	Description	Value	Remarks
C1, C4	multilayer ceramic chip capacitor	10 pF	ATC100A
C2	multilayer ceramic chip capacitor	4.7 μF	
C3, C8, C11	multilayer ceramic chip capacitor	1 nF	ATC100B
C5	multilayer ceramic chip capacitor	5.1 pF	ATC100A
C6, C9	multilayer ceramic chip capacitor	10 pF	ATC800A
C12	electrolytic capacitor	100 μF, 63 V	
C13, C14	multilayer ceramic chip capacitor	10 μF	Murata: GRM55DR61H106KA88L
R1	resistor	5 Ω	SMD 0603

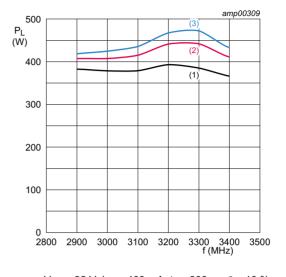
7.4 Graphical data



 V_{DS} = 32 V; I_{Dq} = 400 mA; P_L = 400 W; t_p = 300 $\mu s;$ δ = 10 %.

- (1) G_p
- (2) η_D

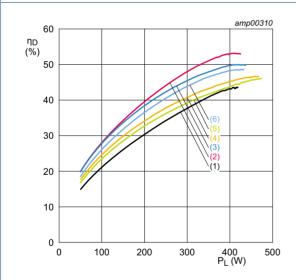
Fig 3. Power gain and drain efficiency as function of frequency; typical values



 V_{DS} = 32 V; I_{Dq} = 400 mA; t_p = 300 $\mu s; \, \delta$ = 10 %.

- (1) P_{1dB}
- (2) P_{2dB}
- (3) P_{3dB}

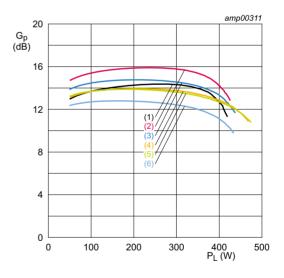
Fig 4. Output power as a function of frequency; typical values



 V_{DS} = 32 V; I_{Dq} = 400 mA; t_p = 300 μ s; δ = 10 %.

- (1) f = 2900 MHz
- (2) f = 3000 MHz
- (3) f = 3100 MHz
- (4) f = 3200 MHz
- (5) f = 3300 MHz
- (6) f = 3400 MHz

Fig 5. Drain efficiency as a function of output power; typical values



 V_{DS} = 32 V; I_{Dq} = 400 mA; t_p = 300 $\mu s; \, \delta$ = 10 %.

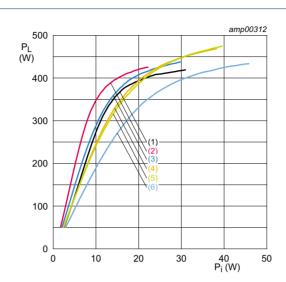
- (1) f = 2900 MHz
- (2) f = 3000 MHz
- (3) f = 3100 MHz
- (4) f = 3200 MHz
- (5) f = 3300 MHz(6) f = 3400 MHz

Fig 6. Power gain as a function of output power; typical values

BLS9G2934L-400_LS-400

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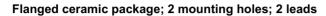


 V_{DS} = 32 V; I_{Dq} = 400 mA; t_p = 300 μ s; δ = 10 %.

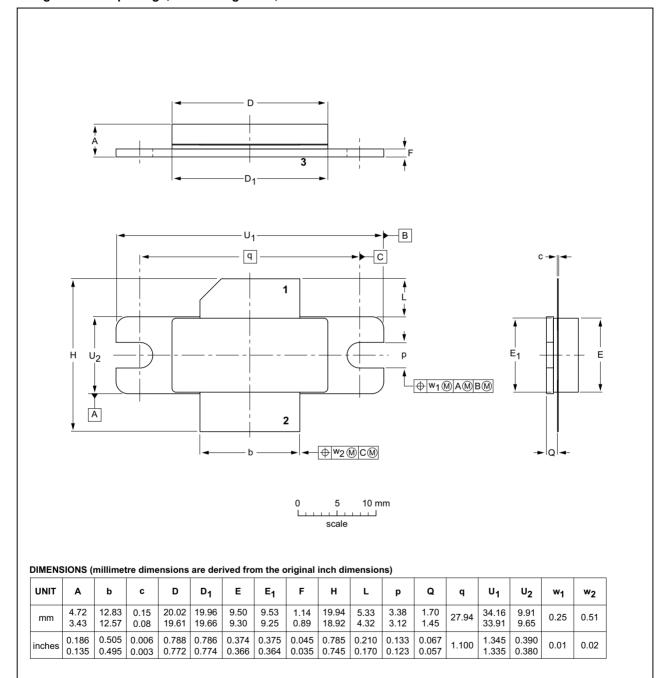
- (1) f = 2900 MHz
- (2) f = 3000 MHz
- (3) f = 3100 MHz
- (4) f = 3200 MHz
- (5) f = 3300 MHz
- (6) f = 3400 MHz

Fig 7. Output power as a function of input power; typical values

8. Package outline



SOT502A



OUTLINE		REFERENCES			EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT502A						-03-01-10 - 12-05-02	

Fig 8. Package outline SOT502A

Earless flanged ceramic package; 2 leads

SOT502B

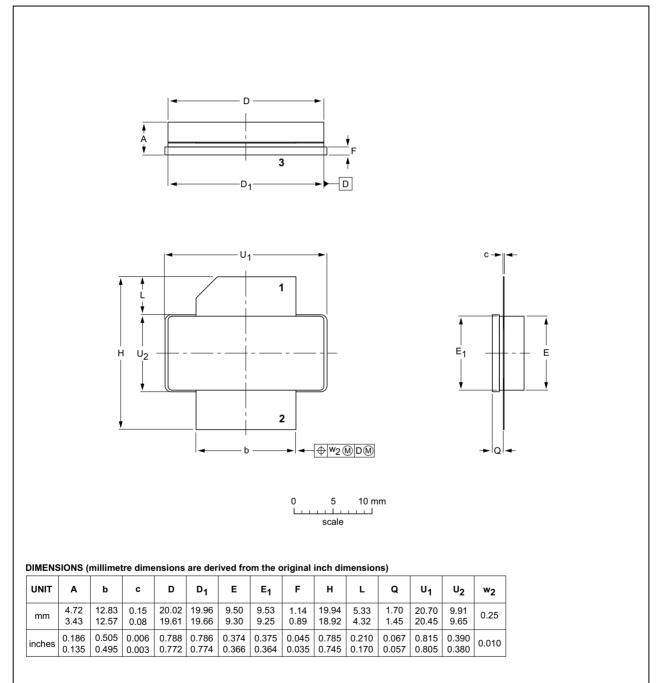


Fig 9. Package outline SOT502B

IEC

OUTLINE

VERSION

SOT502B

JEITA

REFERENCES

JEDEC

ISSUE DATE

07-05-09

12-05-02

EUROPEAN

PROJECTION

Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 10. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

10. Abbreviations

Table 11. Abbreviations

Acronym	Description	
ESD	ElectroStatic Discharge	
LDMOS	aterally Diffused Metal-Oxide Semiconductor	
MTF	Median Time to Failure	
S-band	Short wave Band	
SMD	Surface Mounted Device	
VSWR	Voltage Standing-Wave Ratio	

11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLS9G2934L-400_LS-400 v.1	20170406	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3] Definition	
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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LDMOS S-band radar power transistor

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